



PCN# : P629AAB
Issue Date : Mar. 03, 2016

DESIGN/PROCESS CHANGE NOTIFICATION

This is to inform you that a change is being made to the products listed below.

Unless otherwise indicated in the details of this notification, the identified change will have no impact on product quality, reliability, electrical, visual or mechanical performance and affected products will remain fully compliant to all published specifications. Products incorporating this change may be shipped interchangeably with existing unchanged products.

This change is planned to take effect in 90 calendar days from the date of this notification. Please work with your local Fairchild Sales Representative to manage your inventory of unchanged product if your evaluation of this change will require more than 90 calendar days.

Please contact your local Customer Quality Engineer within 30 days of receipt of this notification if you require any additional data or samples.

Implementation of change:

Expected First Shipment Date for Changed Product :Jun. 01, 2016

Expected First Date Code of Changed Product :1623

Description of Change (From) :
Qualify alternate Assy location

FROM Assembly & Test Site: PSTS China

Assembly Site	PSTS
Package	SOIC – N 8 Ids
Lead frame	Copper with Spot Ag
Die attach	Able 84-1MISR4
Wire	2.0 mil Au wire
Mold Compound	KTMC-5900GM
Terminal Finish	100% tin plate

Description of Change (To) :

TO Assembly & Test Site: Adding HANA AYT, Thailand as alternate sites.

Assembly Site	HANA AYT
Package	SOIC – N 8 lds
Lead frame	Samsung RT UPG1
Die attach	Henkel QMI519
Wire	2.0 mil Au wire
Mold Compound	Hitachi CEL8240HF10LYR
Terminal Finish	NiPdAuAg

Reason for Change:
Improve supply flexibility.

Affected Product(s):

FQS4900TF	FQS4903TF	
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Qualification Plan	Device	Package	Process	No. of Lots
Q20140077	FQA24N60	TO-3PN 3L	Q-FET	3

Test Description:	Condition:	Standard :	Duration:	Results:
High Temperature Reverse Bias	150C, 400V (80% BV)	JESD22-A108	1000 hrs	0/231
High Temperature Reverse Bias	150C, 600V (100% BV)	JESD22-A108	1000 hrs	0/231
High Temperature Gate Bias	150C, 30V	JESD22-A108	1000 hrs	0/231
Highly Accelerated Stress Test	85%RH, 130C, 42V	JESD22-A110	96 hrs	0/231
Temperature Cycle	-65C, 150C	JESD22-A104	500 cycles	0/231
Power Cycle	Delta 100C, 2 Min cycle	MIL-STD-750-1036	6000 cycles	0/77
High Temperature Storage Life	150C	JESD22-A103	1000 hrs	0/231

Qualification Plan	Device	Package	Process	No. of Lots
Q20150060	FDS8949_F085	SO8	PT 4N	2

Test Description:	Condition:	Standard :	Duration:	Results:
Highly Accelerated Stress Test	85%RH, 130C, 42V	JESD22-A110	96 hrs	0/154
High Temperature Reverse Bias	150C, 40V	JESD22-A108	1000 hrs	0/154
High Temperature Gate Bias	150C, 20V	JESD22-A108	1000 hrs	0/154
High Temperature Storage Life	150C	JESD22-A103	1000 hrs	0/231
Power Cycle	Delta 100C, 2 Min cycle	MIL-STD-750-1036	15000 cycles	0/154
Temperature Cycle	-65C, 150C	JESD22-A104	500 cycles	0/154
Unbias Highly Accelerated Stress Test	85%RH, 130C	JESD22-A118	96 hrs	0/154
MSLNL1A	PeakTemp(260°C), Cycles 3X	J-STD-020	-	0/44
Resistance to Solder Heat	260°C	JESD22-B106	3X @ 10s	0/20
Solderability, Condition B	245°C, 5 sec	JESD22-B102	8 hrs	0/20

Qualification Plan	Device	Package	Process	No. of Lots
Q20160089	FQS4903TF	SO8	Q-FET	1

Test Description:	Condition:	Standard :	Duration:	Results:
High Temperature Reverse Bias	150C, 400V	JESD22-A108	1000 hrs	0/77
High Temperature Storage Life	150C	JESD22-A103	1000 hrs	0/77
Temperature Humidity Bias Test	85%RH, 85C, 100V	JESD22-A101	1000 hrs	0/77
Temperature Cycle	-65C, 150C	JESD22-A104	500 cycles	0/77
Unbias Highly Accelerated Stress Test	85%RH, 130C	JESD22-A118	96 hrs	0/77
MSLNL1A	PeakTemp(260°C), Cycles 3X	J-STD-020	-	0/11